



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Naoto Kusumoto et al.
Serial No. : 10/602,762
Filed : June 25, 2003
Title : LASER ANNEALING METHOD

Art Unit : 2828
Examiner : Delma Flores Ruiz

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUBMISSION OF CORRECTED FORM PTO-1449

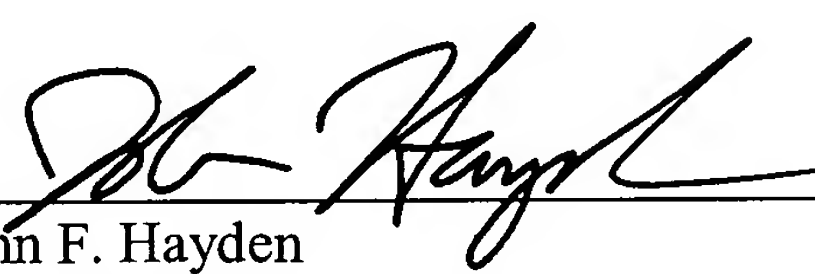
Supplemental to an information disclosure statement filed with the application on June 25, 2003, applicants submit the attached corrected Form PTO-1449. All of the documents listed on the form PTO-1449 were cited in the information disclosure statement filed with the application. The corrected Form PTO-1449 is being submitted to correctly recite the country for reference "AU" as "South Africa" instead of "China."

No fees are believed to be due. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

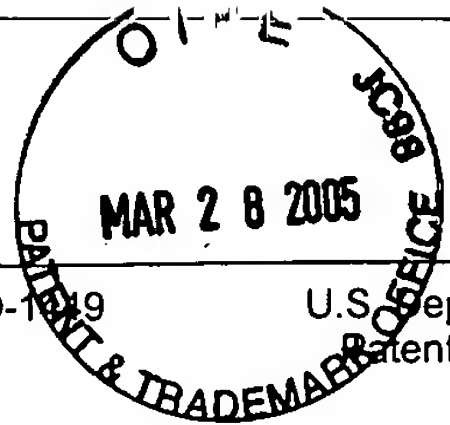
Date: _____

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| Substitute Form PTO-1449 (Modified) Corrected Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b)) | U.S. Department of Commerce Patent and Trademark Office | Attorney's Docket No. 07977-004002 | Application No. 10/602,762 |
| | Applicant Naoto Kusumoto et al. | | |
| | Filing Date June 25, 2003 | Group Art Unit 2828 | |

| U.S. Patent Documents | | | | | | | |
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| Examiner Initial | Desig. ID | Document Number | Publication Date | Patentee | Class | Subclass | Filing Date If Appropriate |
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| | | | | | | | Yes | No |
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| Examiner Signature | Date Considered |
| EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |



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| | Applicant Naoto Kusumoto et al. | | |
| | Filing Date June 25, 2003 | Group Art Unit 2828 | |

| Foreign Patent Documents or Published Foreign Patent Applications | | | | | | | | |
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| Examiner Initial | Desig. ID | Document Number | Publication Date | Country or Patent Office | Class | Subclass | Translation | |
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| | AKK | Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; <i>Optical Eng.</i> 31(2); p. 245; February 1992 |

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| Examiner Signature | Date Considered |
| EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |